

IN THE CLAIMS:

Kindly cancel claims 3 and 7 without prejudice or disclaimer. A detailed listing of all claims is as follows.

Claim 1 (Previously Presented): A method for forming silicon quantum dots comprising the steps of:

forming a first insulating film on a semiconductor substrate;
forming a plurality of nano-crystalline silicons on the first insulating film;
forming a second insulating film on the first insulating film including the nano-crystalline silicons;
partially etching the second insulating film and the nano-crystalline silicons; and
oxidizing surfaces of the etched nano-crystalline silicons.

Claim 2 (Original): The method of claim 1, wherein the nano-crystalline silicons are formed at a size of about 30nm.

Claim 3 (Canceled).

Claim 4 (Original): The method of claim 1, wherein the nano-crystalline silicons are oxidized by about 5nm.

Claim 5 (Original): A method for fabricating a nonvolatile memory device comprising the steps of:

forming a tunnelling insulating film on a semiconductor substrate;
forming a plurality of nano-crystalline silicons on the tunnelling insulating film;
forming a first insulating film on the tunnelling insulating film including the
nano-crystalline silicons;
partially etching the first insulating film and the nano-crystalline silicons;
oxidizing surfaces of the nano-crystalline silicons;
forming a second insulating film on the first insulating film including the nano-crystalline
silicons;
forming a control gate on the second insulating film;
removing the second insulating film, the nano-crystalline silicons, and the tunnelling
insulating film using the control gate as a mask; and
forming impurity regions in a surface of the semiconductor substrate at both sides of the
control gate.

Claim 6 (Original): The method of claim 5, wherein the nano-crystalline silicons are
formed at a size of about 30nm.

Claim 7 (Canceled).

Claim 8 (Original): The method of claim 5, wherein the nano-crystalline silicons are
oxidized by about 5nm.